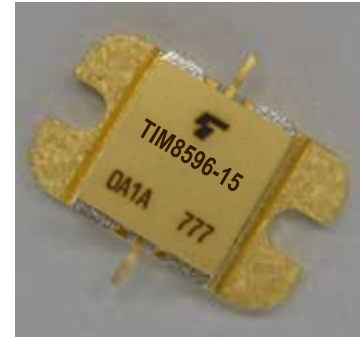


**FEATURES**

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER  
P1dB= 42.0dBm at 8.5GHz to 9.6GHz
- HIGH GAIN  
G1dB= 7.0dB at 8.5GHz to 9.6GHz
- HERMETICALLY SEALED PACKAGE



**RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V IDSset= 4.0A f= 8.5 to 9.6GHz	dBm	41.0	42.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	7.0	—
Drain Current	IDS		A	—	4.5	5.5
Power Added Efficiency	$\eta_{add}$		%	—	31	—
Channel Temperature Rise	$\Delta T_{ch}$		$(VDS \times IDS + P_{in} - P_{1dB}) \times R_{th(c-c)}$	°C	—	—

**Recommended Gate Resistance(Rg): 100 Ω**

**ELECTRICAL CHARACTERISTICS ( Ta= 25°C )**

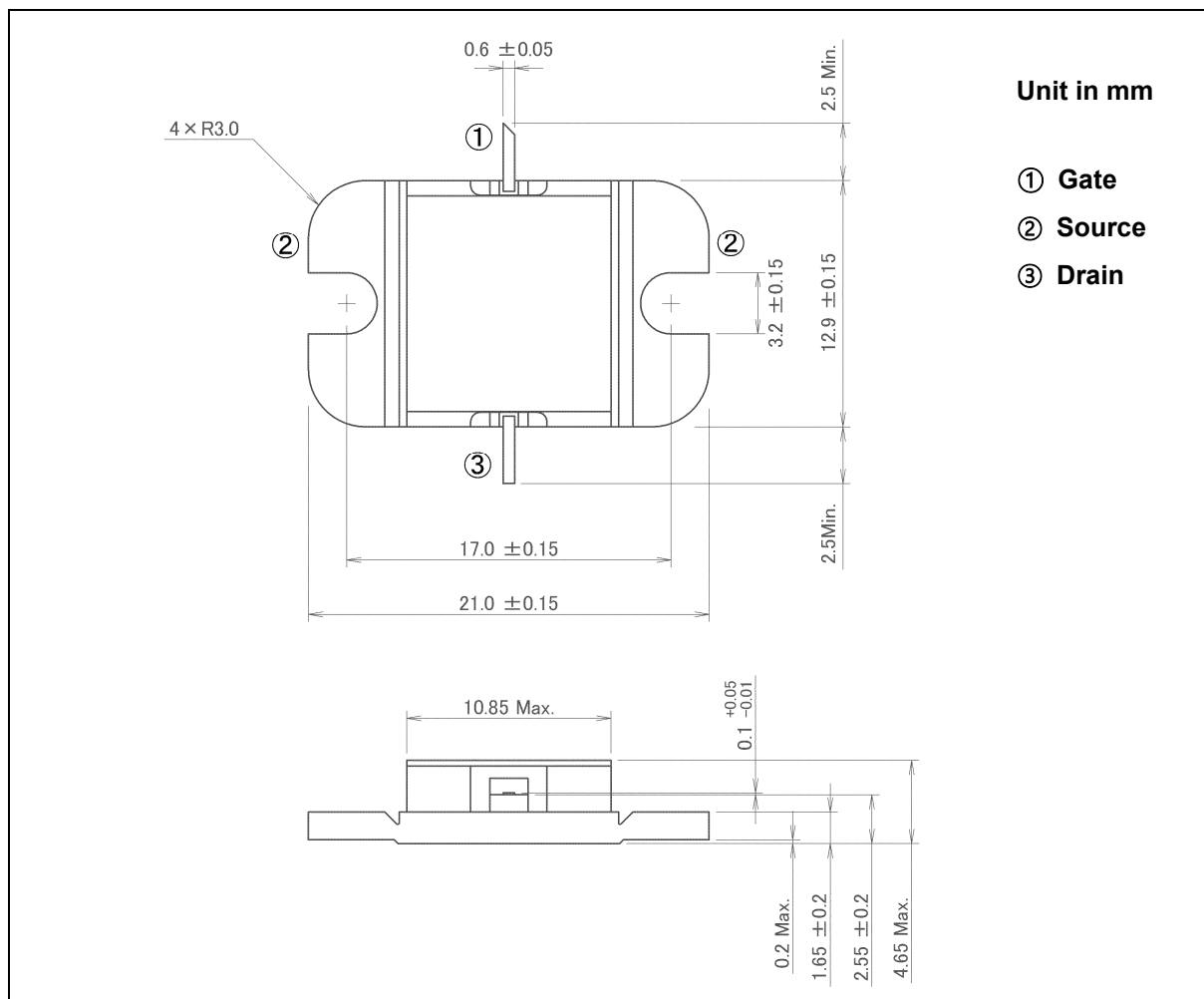
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	S	—	3.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	—
Gate-Source Breakdown Voltage	VGS0	IGS= --145μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

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**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	10.4
Total Power Dissipation (Tc= 25°C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-11C1B)**



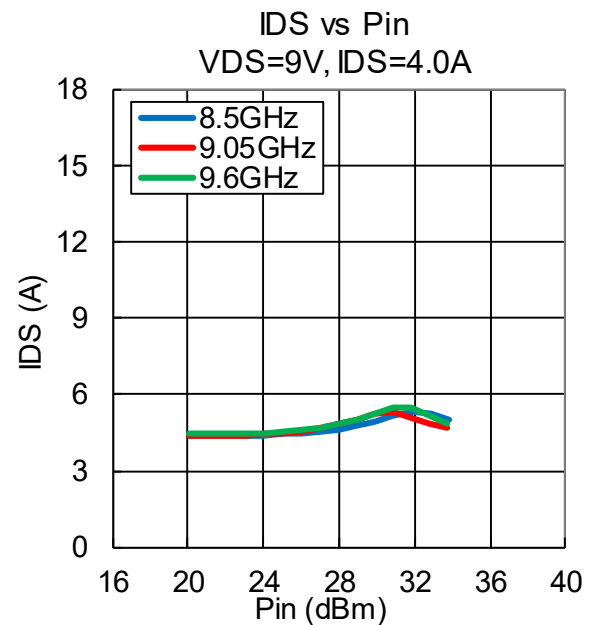
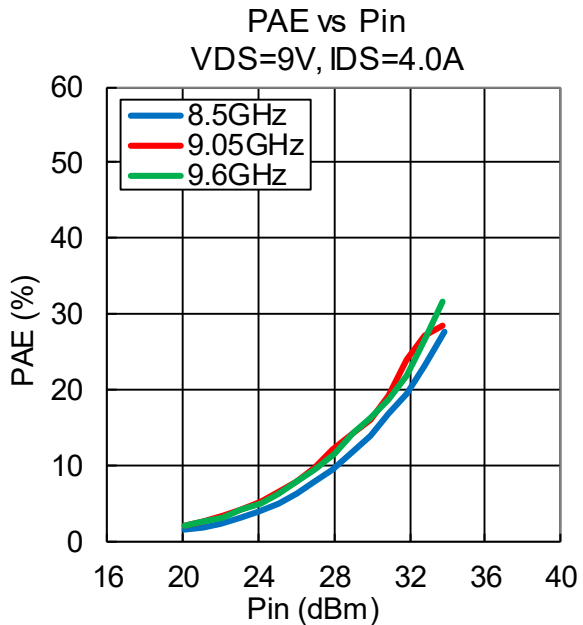
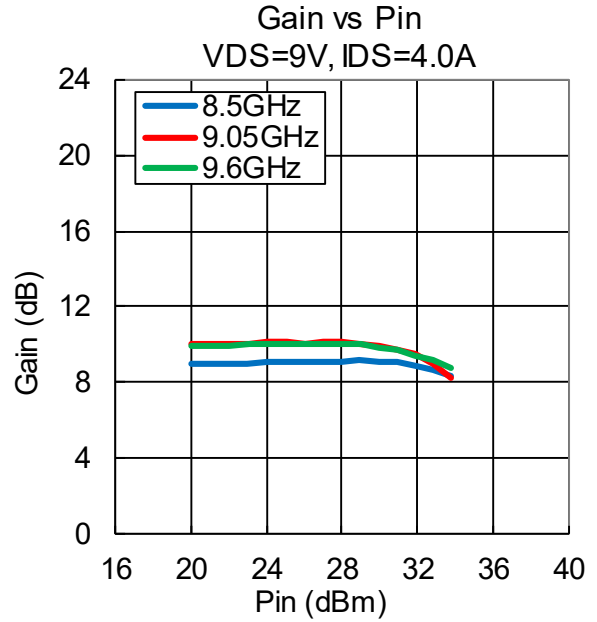
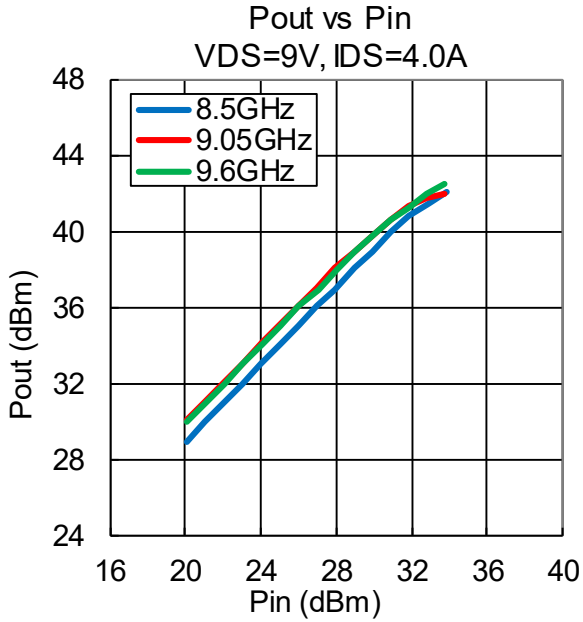
**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**TYPICAL RF PERFORMANCE**

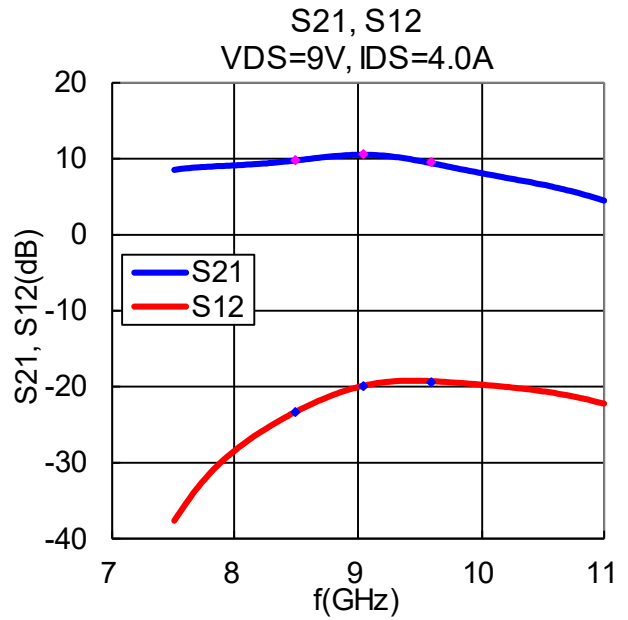
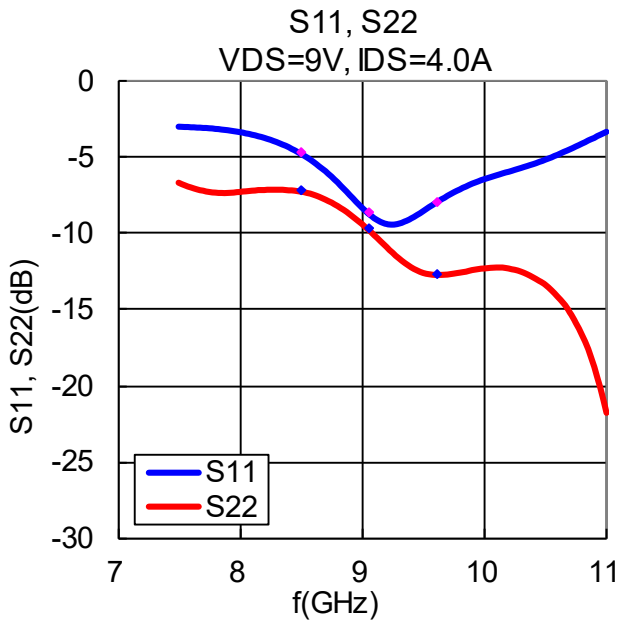
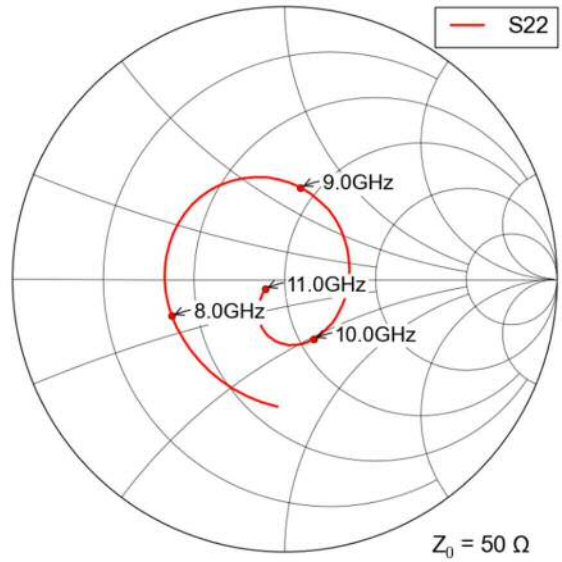
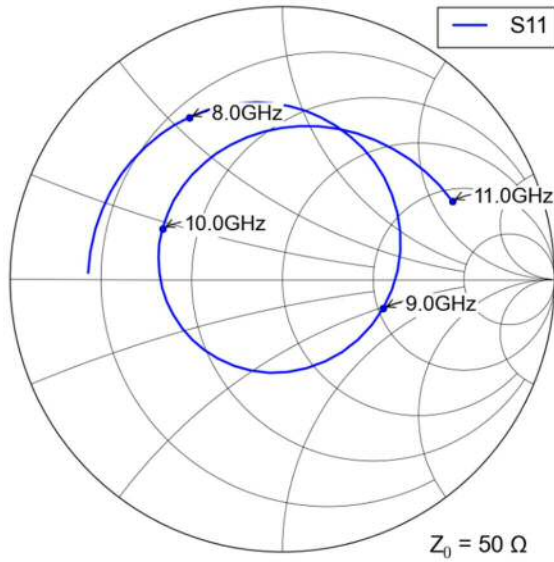
•Pout , Gain , PAE , IDS vs. Pin

VDS= 9 V, IDSset= 4.0 A, f= 8.5, 9.05, 9.6 GHz, Ta= +25 °C



**-S-Parameters**

VDS= 9 V, IDSset= 4.0 A, f= 7.5 to 11.0 GHz, Ta= +25 °C



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